# Supertex inc.



#### Features

- Free from secondary breakdown
- Low power drive requirement
- Ease of paralleling
- Low C<sub>ISS</sub> and fast switching speeds
- High input impedance and high gain
- Excellent thermal stability
- Integral source-to-drain diode
- High input impedance and high gain
- Complementary N- and P-channel devices

#### **Applications**

- Motor controls
- Converters
- Amplifiers
- Switches
- Power supply circuits
- Drivers (relays, hammers, solenoids, lamps, memories, displays, bipolar transistors, etc.)

#### **Ordering Information**

#### **General Description**

The Supertex VP0104 is an enhancement-mode (normallyoff) transistor that utilizes a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors, and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Device	Package Option	BV <sub>DSS</sub> /BV <sub>DGS</sub>	R <sub>DS(ON)</sub>	l <sub>D(ON)</sub> (min) (mA)	
Device	TO-92	(V)	(max) (Ω)		
VP0104	VP0104N3-G	-40	8.0	-500	

Value

+300°C

-G indicates package is RoHS compliant ('Green')

**Absolute Maximum Ratings** 



Drain-to-source voltage

Soldering temperature\*

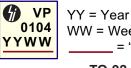
Parameter

#### **Pin Configuration**



TO-92 (N3)

#### **Product Marking**



YY = Year Sealed WW = Week Sealed = "Green" Packaging TO-92 (N3)

#### **BV**<sub>DSS</sub> Drain-to-gate voltage BV Gate-to-source voltage ±20V Operating and storage temperature -55°C to +150°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

\* Distance of 1.6mm from case for 10 seconds.

#### **Thermal Characteristics**

Package	I <sub>D</sub> (continuous) <sup>†</sup> (mA)	Ι <sub>D</sub> (pulsed) (mA)	Power Dissipation @T <sub>c</sub> = 25°C (W)	θ <sub>jc</sub> (°C/W)	θ <sub>ja</sub> (°C/W)	l <sub>DR</sub> † (mA)	I <sub>DRM</sub> (mA)
TO-92	-250	-800	1.0	125	170	-250	-800

Notes:

 $\uparrow I_{D}$  (continuous) is limited by max rated  $T_{i}$ .

#### **Electrical Characteristics** ( $T_A = 25^{\circ}C$ unless otherwise specified)

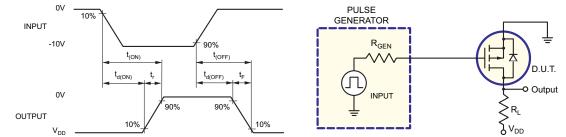
<b>Electrical Gharacteristics</b> $\{I_A = 25 \text{ Curress otherwise specified}\}$								
Sym	Parameter	Min	Тур	Max	Units	Conditions		
BV <sub>DSS</sub>	Drain-to-source breakdown voltage	-40	-	-	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -1.0mA		
V <sub>GS(th)</sub>	Gate threshold voltage	-1.5	-	-3.5	V	$V_{gs} = V_{Ds}, I_{D} = -1.0 mA$		
$\Delta V_{GS(th)}$	Change in $V_{GS(th)}$ with temperature	-	5.8	6.5	mV/ºC	$V_{gs} = V_{Ds}, I_{D} = -1.0 mA$		
I <sub>GSS</sub>	Gate body leakage current	-	-1.0	-100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$		
		-	-	-10	μA	$V_{GS}$ = 0V, $V_{DS}$ = Max Rating		
I <sub>DSS</sub>	Zero gate voltage drain current	-	-	-1.0	mA	$V_{DS} = 0.8$ Max Rating, $V_{GS} = 0V$ , $T_A = 125^{\circ}C$		
		-0.15	-0.25	-		V <sub>GS</sub> = -5.0V, V <sub>DS</sub> = -25V		
I <sub>D(ON)</sub>	On-state drain current	-0.5	-1.2	-	A	V <sub>GS</sub> = -10V, V <sub>DS</sub> = -25V		
Р	Static drain-to-source on-state resistance	-	11	15	Ω	V <sub>GS</sub> = -5.0V, I <sub>D</sub> = -100mA		
R <sub>DS(ON)</sub>		-	6.0	8.0		V <sub>GS</sub> = -10V, I <sub>D</sub> = -500mA		
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with temperature	-	0.55	1.0	%/°C	V <sub>GS</sub> = -10V, I <sub>D</sub> = -500mA		
G <sub>FS</sub>	Forward transconductance	150	190	-	mmho	V <sub>DS</sub> = -25V, I <sub>D</sub> = -500mA		
C <sub>ISS</sub>	Input capacitance	-	45	60		V <sub>GS</sub> = 0V,		
C <sub>oss</sub>	Common source output capacitance	-	22	30	pF	$V_{DS} = -25V,$		
C <sub>RSS</sub>	Reverse transfer capacitance	-	3.0	8.0		f = 1.0MHz		
t <sub>d(ON)</sub>	Turn-on time	-	4.0	6.0		$V_{DD} = -25V,$		
t,	Rise time	-	3.0	10	nc			
t <sub>d(OFF)</sub>	Turn-off time	-	8.0	12	ns	$I_{D} = -500 \text{mA},$ $R_{GEN} = 25\Omega$		
t <sub>r</sub>	Fall time	-	4.0	10		GEN		
V <sub>SD</sub>	Diode forward voltage drop	-	-1.2	-2.0	V	V <sub>GS</sub> = 0V, I <sub>SD</sub> = -1.0A		
t <sub>rr</sub>	Reverse recovery time	-	400	-	ns	V <sub>GS</sub> = 0V, I <sub>SD</sub> = -1.0A		

Notes:

1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)

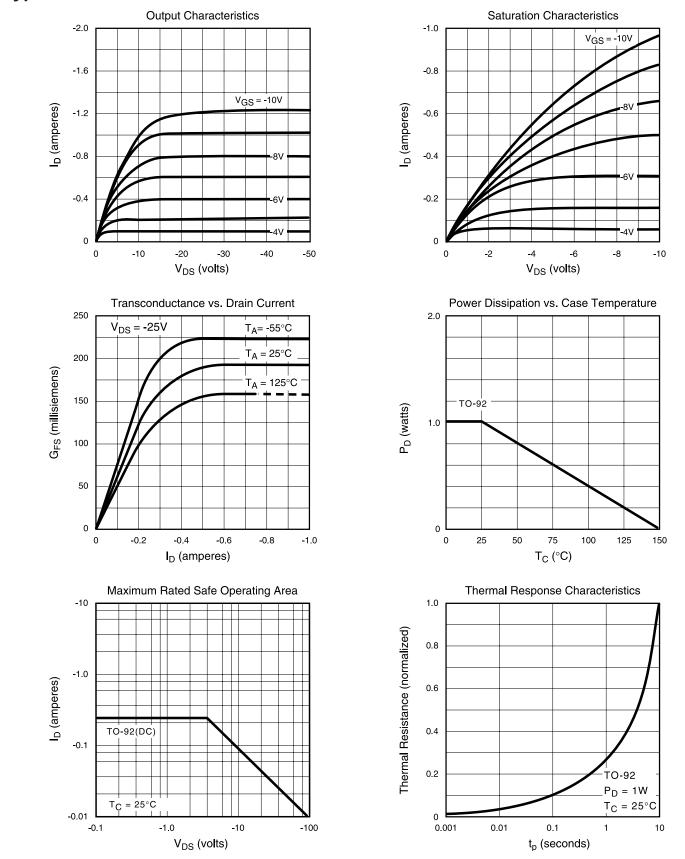
2. All A.C. parameters sample tested.

#### **Switching Waveforms and Test Circuit**



Supertex inc. • 1235 Bordeaux Drive, Sunnyvale, CA 94089 • Tel: (408) 222-8888 • FAX: (408) 222-4895 • www.supertex.com

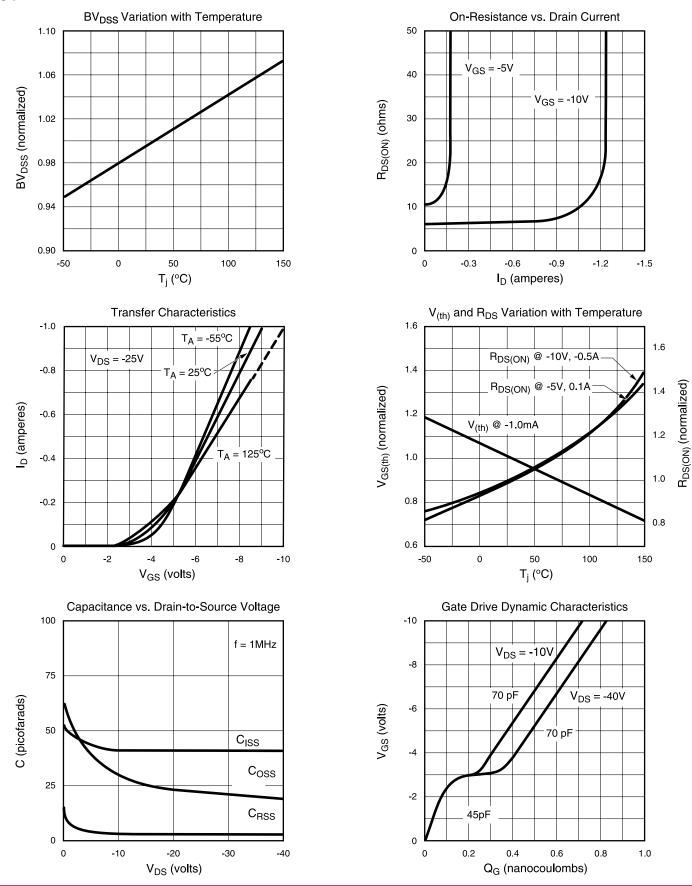
#### VP0104



#### **Typical Performance Curves**

Supertex inc. • 1235 Bordeaux Drive, Sunnyvale, CA 94089 • Tel: (408) 222-8888 • FAX: (408) 222-4895 • www.supertex.com

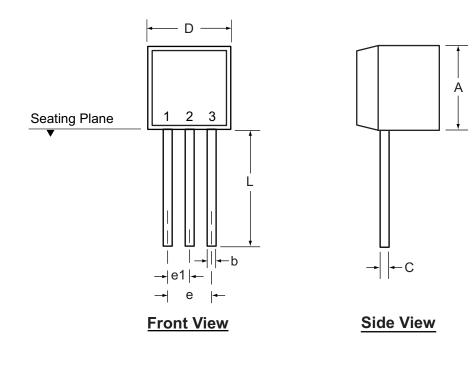
### VP0104

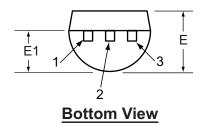


#### Typical Performance Curves (cont.)

Supertex inc. • 1235 Bordeaux Drive, Sunnyvale, CA 94089 • Tel: (408) 222-8888 • FAX: (408) 222-4895 • www.supertex.com

## 3-Lead TO-92 Package Outline (N3)





Symbol		Α	b	С	D	E	E1	е	e1	L
Dimension (inches)	MIN	.170	.014	.014	.175	.125	.080	.095	.045	.500
	NOM	-	-	-	-	-	-	-	-	-
	MAX	.210	.022	.022	.205	.165	.105	.105	.055	-

Drawings not to scale.

(The package drawing (s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <u>http://www.supertex.com/packaging.html</u>.)

**Supertex inc.** does not recommend the use of its products in life support applications, and will not knowingly sell its products for use in such applications, unless it receives an adequate "product liability indemnification insurance agreement". **Supertex** does not assume responsibility for use of devices described and limits its liability to the replacement of the devices determined defective due to workmanship. No responsibility is assumed for possible omissions or inaccuracies. Circuitry and specifications are subject to change without notice. For the latest product specifications, refer to the **Supertex** website: http://www.supertex.com.

©2008 Supertex inc. All rights reserved. Unauthorized use or reproduction is prohibited.

Doc.# DSFP-VP0104 A020408

